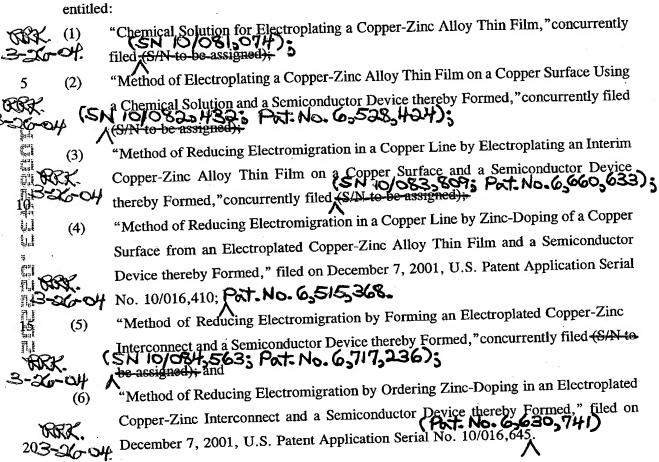
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## METHOD OF CONTROLLING ZINC-DOPING IN A COPPER-ZINC ALLOY THIN FILM ELECTROPLATED ON A COPPER SURFACE AND A SEMICONDUCTOR DEVICE THEREBY FORMED

## CROSS-REFERENCE TO RELATED APPLICATION(S)

[0001] This application is also related to the following commonly assigned applications, entitled:



## TECHNICAL FIELD

[0002] The present invention relates to semiconductor devices and their methods of fabrication. More particularly, the present invention relates to the processing of copper interconnect material and the resultant device utilizing the same. Even more particularly, the present invention relates to reducing electromigration in copper interconnect lines by doping their surfaces with a barrier material using wet chemical methods.